

<b>Notice of References Cited</b>		Application/Control No. 09/776,009	Applicant(s)/Patent Under Reexamination VYVODA ET AL.	
		Examiner Anh D. Mai	Art Unit 2814	Page 1 of 1

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.